

Product Summary

BV _{DSS}	Rds(on) Max	I _D Max Tc = +25°C		
40V	12.3mΩ @ V _{GS} = 10V	46.2A		
400	17.5mΩ @ V _{GS} = 4.5V	38.7A		

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Motor Control
- Power Management Functions
- DC-DC Converters

Features and Benefits

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching, Test in Production– Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low R_{DS(ON)} Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- Wettable Flank for Improved Optical Inspection
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMTH4008LPDWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

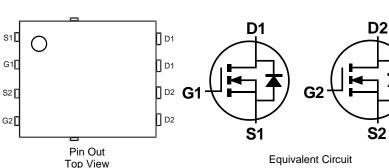
https://www.diodes.com/guality/product-definitions/

Mechanical Data

- Case: PowerDI[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)

PowerDI5060-8/SWP (Type UXD)





Ordering Information (Note 4)

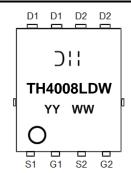
Part Number	Case	Packaging		
DMTH4008LPDWQ-13	PowerDI5060-8/SWP (Type UXD)	2,500/Tape & Reel		

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
See http://www.diodes.com/quality/lead_free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free

3. Halogen and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.</p>

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



)'' = Manufacturer's Marking TH4008LDW = Product Type Marking Code YYWW or $\overline{YY}WW$ = Date Code Marking YY or \overline{YY} = Year (ex: 20 = 2020) WW = Week (01 to 53)



Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	40	V	
Gate-Source Voltage	Vgss	±20	V	
Continuous Drain Current (Note 5)	T _A = +25°C T _A = +100°C	lD	10.0 7.1	A
Continuous Drain Current (Note 6)	T _C = +25°C T _C = +100°C	ID	46.2 32.7	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	Ідм	184	A	
Maximum Continuous Body Diode Forward Current (Note 6)	ls	43.7	A	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle	I _{SM}	184	A	
Avalanche Current, L = 0.1mH	las	23.1	A	
Avalanche Energy, L = 0.1mH	Eas	26.6	mJ	

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	PD	2.67	W	
Thermal Resistance, Junction to Ambient (Note 5)		Reja	56.6	°C/W
Total Power Dissipation (Note 6) $T_{C} = +25^{\circ}C$		PD	39.4	W
Thermal Resistance, Junction to Case (Note 6)	R _{eJC}	3.8	°C/W	
Operating and Storage Temperature Range		TJ, TSTG	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

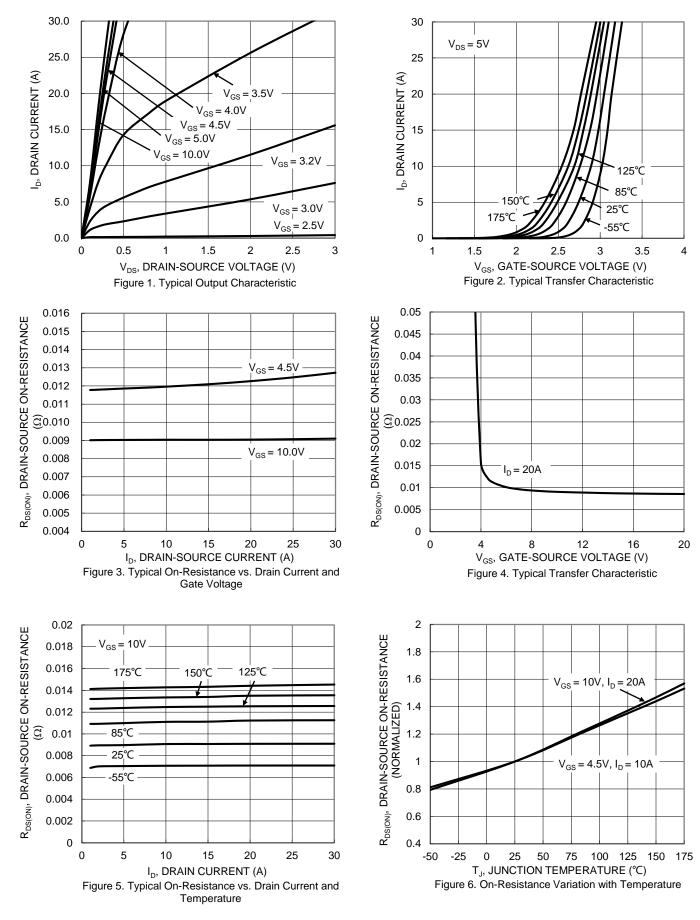
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BVDSS	40	—	_	V	$V_{GS} = 0V, I_D = 250 \mu A$	
Zero Gate Voltage Drain Current	IDSS	_	—	1	μA	V _{DS} = 32V, V _{GS} = 0V	
Gate-Source Leakage	IGSS	_	—	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)						•	
Gate Threshold Voltage	Vgs(th)	1.2	1.88	2.3	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	
Static Drain-Source On-Resistance	Descent	—	9.5	12.3	mΩ	Vgs = 10V, Ip = 20A	
Static Drain-Source On-Resistance	RDS(ON)	—	11.9	17.5	mΩ	VGS = 4.5V, ID = 10A	
Diode Forward Voltage	V _{SD}	_	0.9	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)			•			•	
Input Capacitance	Ciss	_	881	—	pF	$V_{DS} = 20V, V_{GS} = 0V,$ f = 1MHz	
Output Capacitance	Coss	_	496	_	pF		
Reverse Transfer Capacitance	Crss	_	19.5	-	pF		
Gate Resistance	Rg	_	2.06	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V _{GS} = 10V)	Qg	_	12.3	_	nC		
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	5.8	_	nC		
Gate-Source Charge	Qgs	_	2.6	_	nC	$V_{DS} = 20V, I_{D} = 20A$	
Gate-Drain Charge	Q _{gd}		1.6		nC	1	
Turn-On Delay Time	t _{D(ON)}	_	3.82		ns	V _{DD} = 20V, V _{GS} = 10V,	
Turn-On Rise Time	tR	_	4.76	_	ns		
Turn-Off Delay Time	tD(OFF)	_	12.6		ns	$R_g = 3\Omega$, $I_D = 20A$	
Turn-Off Fall Time	tF	_	4.83	_	ns	1	
Body Diode Reverse Recovery Time	trr	_	31.9	_	ns		
Body Diode Reverse Recovery Charge	Q _{RR}	_	25.0	—	nC	I _F = 20A, di/dt = 100A/µs	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz. copper, with thermal bias to bottom layer 1inch square copper plate.

Device involution of the substrate For board, 202. copper, with the main bas to
Thermal resistance from junction to soldering point (on the exposed drain pad).
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing.



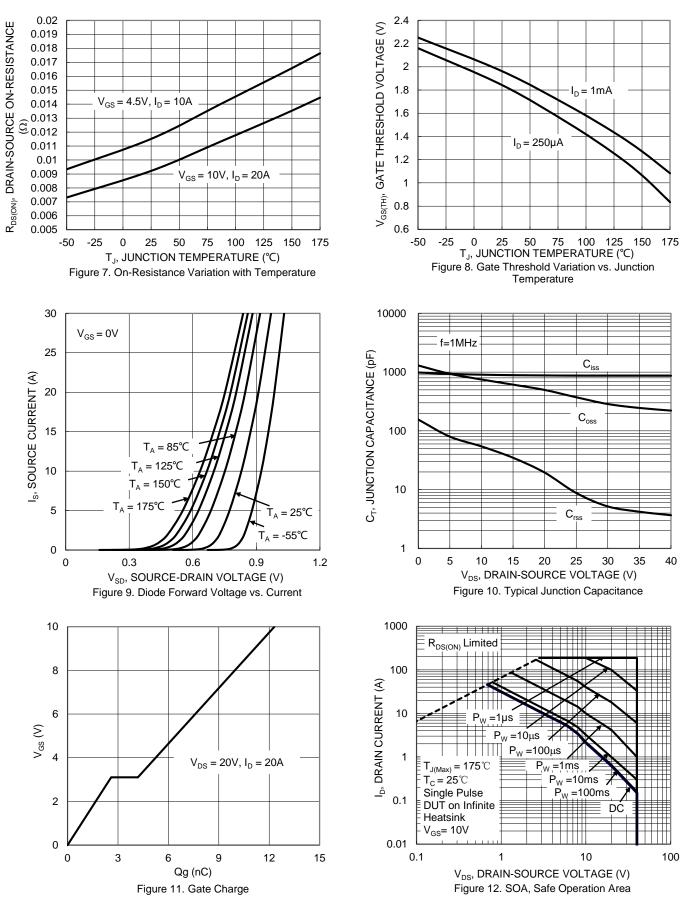
DMTH4008LPDWQ



DMTH4008LPDWQ Document number: DS41691 Rev. 4 - 2

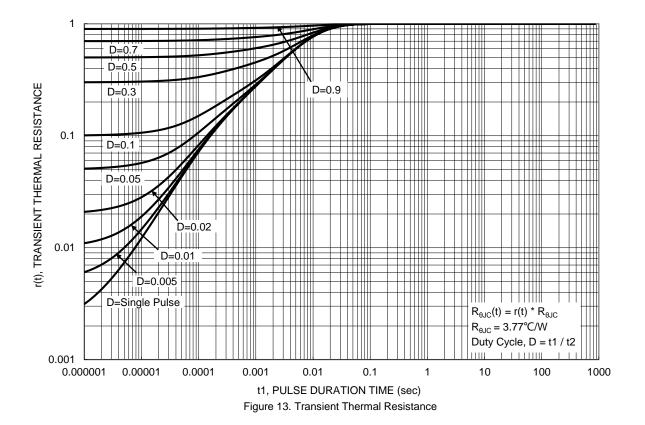


DMTH4008LPDWQ







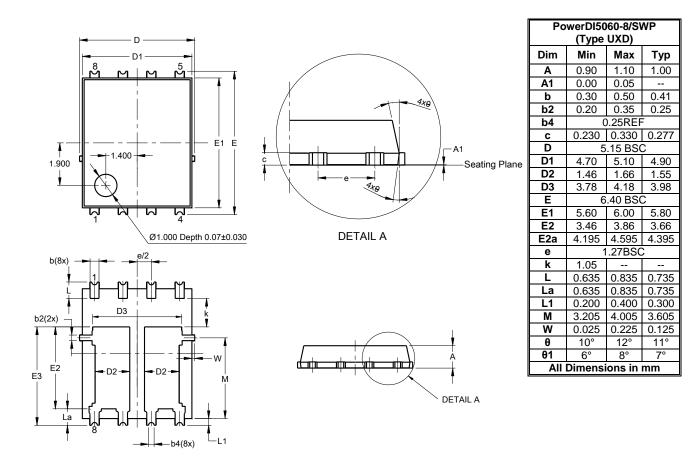




Package Outline Dimensions

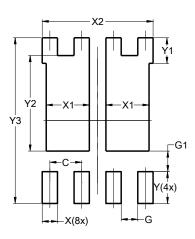
Please see http://www.diodes.com/package-outlines.html for the latest version.





Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



PowerDI5060-8/SWP (Type UXD)

Dimensions	Value (in mm)		
С	1.270		
G	0.660		
G1	0.820		
Х	0.610		
X1	1.720		
X2	4.420		
Y	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		



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